QS120C080Y4: 1200V N-Channel SiC MOSFET

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Description

- FAST SWITCHING WITH LOW EMI/RFI
- LOW GATE CHARGE MINIMIZE SWITCHING LOSS
- SHORT CIRCUIT WITHSTAND RATED
- LOW RDS(ON) TEMPERATURE COEFFICIENT FOR IMPROVE EFFICIENCY

Applications

- ASYMMETRICAL BRIDGE
- CONVERTER
- INVERTER
- SINGLE SWITCH FORWARD
- FLYBACK
- PV INVERTER (STRING SOLAR INVERTER)
- EV CHARGING PILE

Part Number

QS120C080Y4

Package

TO-247-4L

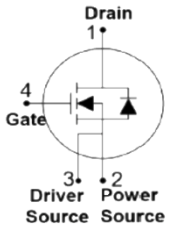
Marking

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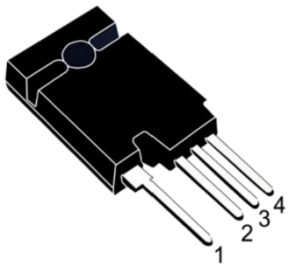
Features

PARAMETER	VALUE	UNIT
BV_{DSS}	1200	V
$R_{DS(ON),typ}$ $(20V)$	80	mΩ
$V_{GS(TH),typ}$	2.8	V
E_{ON}	325	μJ
E_{OFF}	219	μJ
I_D $(at\ 25℃)$	36	A

Package



RoHS



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ABSOLUTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	1200	V
Maximum Gate-to-Source Voltage	V_{GSmax}	$-10 \sim +25$	
Recommended operations values of gate to source voltage	$V_{GSop(DC)}$	$-5.0 \sim +20$	
Recommended operations values of gate to source voltage (f>1Hz)	$V_{GSop(AC)}$	$-5.0 \sim +20$	
Continuous Drain Current	I_D	36.0	A
Continuous Drain Current at $\boldsymbol{T_c = 100}$℃		25.0	
Pulsed Drain Current at $\boldsymbol{VGS = 10V^2}$	I_{DM}	90	
Single Pulse Avalanche Energy $(\boldsymbol{V_{DD} = 50V, V_{GS} = 15V, R_G = 25\Omega, L = 1mH})$	E_{AS}	171	mJ
Power Dissipation	P_D	198	W
Derating Factor above 25°C		1.30	℃/W
Soldering Temperature, Distance of 1.6mm from case for 10 seconds	T_L	300	℃
Operating and Storage Temperature Range	T_J, T_{STG}	$-55\ to\ 175$	
Caution: Stresses greater than those listed in the Absolute Maximum Ratings may cause permanent damage to devices.			
Thermal Characteristics			
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.76	℃/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	

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ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			Unit
			Min	Typ	Max	
OFF Characteristics (T_J = 25°C unless otherwise specified)						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 100\mu A$	1200	–	–	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = 1200V, V_{GS} = 0V$	–	–	100	μA
Gate-to-Source Leakage Current	I_{Gss+}	$V_{DS} = 0V, V_{GS} = 20V$	–	–	100	nA
Gate-to-Source Leakage Current	I_{Gss-}	$V_{DS} = 0V, V_{GS} = -10V$	–	–	−100	nA
ON Characteristics (T_J = 25°C unless otherwise specified)						
Static Drain-to-Source On Resistance [3]	$R_{DS(ON)}$	$V_{GS} = 20V, I_D = 20A$	–	80	100.0	$m\Omega$
		$V_{GS} = 20V, I_D = 20A, T_J = 150°C$	–	121	–	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 5mA$	1.8	2.8	3.8	V
Dynamic Characteristics (Essentially independent of operating temperature)						
Input Capacitance	C_{iss}	$V_{GS} = 0V$ $V_{DS} = 800V$ $f = 1MHz$	–	1001	–	pF
Reverse Transfer Capacitance	C_{rss}		–	7.2	–	
Output Capacitance	C_{oss}		–	60	–	
Gate Series Resistance	R_g	$f = 1MHz$	–	5.6	–	Ω
Total Gate Charge	Q_g	$V_{DD} = 600V$ $I_D = 20A$ $V_{GS} = -\frac{5}{20V}$	–	60	–	nC
Gate-to-Source Charge	Q_{gs}		–	16	–	
Gate-to-Drain (Miller) Charge	Q_{gd}		–	23	–	
Resistive Switching Characteristics (Essentially independent of operating temperature)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 800V$ $I_D = 20A$ $V_{GS} = -\frac{5}{20V}$ $R_G = 4.7\Omega$ $L = 500\mu H$	–	11	–	nS
Rise Time	t_{rise}		–	37	–	
Turn-off Delay Time	$t_{d(off)}$		–	24	–	
Fall Time	t_{fall}		–	9.8	–	
Turn-On Switching Energy	E_{ON}		–	325	–	mJ
Turn-Off Switching Energy	E_{OFF}		–	219	–	
Source-Drain Body Diode Characteristics (T_J = 25°C unless otherwise specified)						
Continuous Source Current	I_{SD}	$Maximum\ Ratings$	–	–	36	A
Diode Forward Voltage	V_{SD}	$I_S = 0.5A, V_{GS} = 0V$	–	2.6	–	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V$ $I_F = 20A$ $\frac{di}{dt} = 800A/\mu s$	–	20	–	nS
Reverse Recovery Charge	Q_{rr}		–	39	–	nC
Peak Reverse Recovery Charge	I_{mm}		–	2.8	–	A

- TJ=25°C to 175°C

- Repetitive rating, pulse width limited by maximum junction temperature

-Pulse width≤380μs; duty cycle≤2%

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Figure 1: Maximum effective Thermal impedance, junction - to - Case

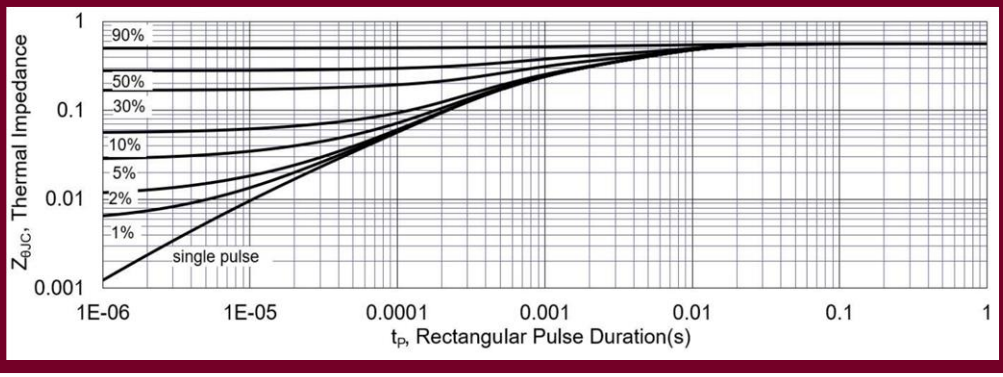


Figure 2: Maximum Power Dissipation vs Case Temperature

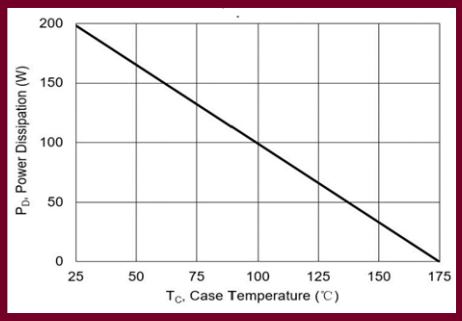


Figure 3: Maximum Continuous Drain Current vs Case Temperature

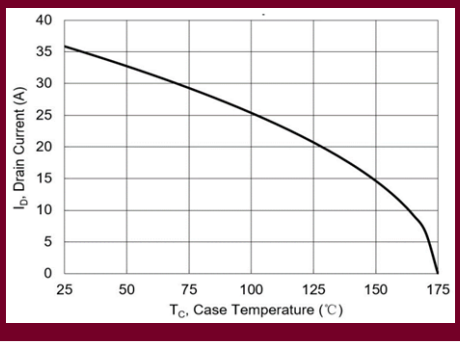


Figure 4: Typical Output Characteristics

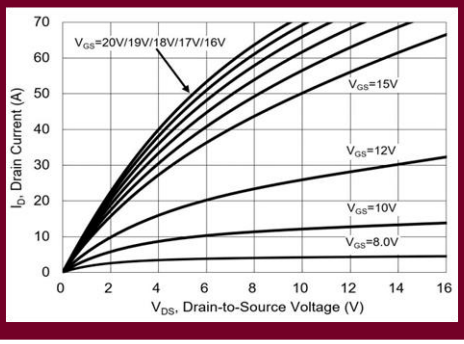
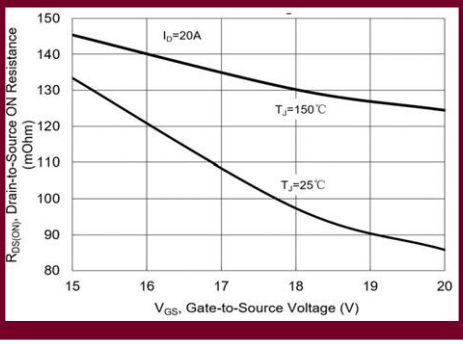


Figure 5: Typical Drain-to-Source ON Resistance vs Gate Voltage



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Figure 6: Maximum Peak Current Capability

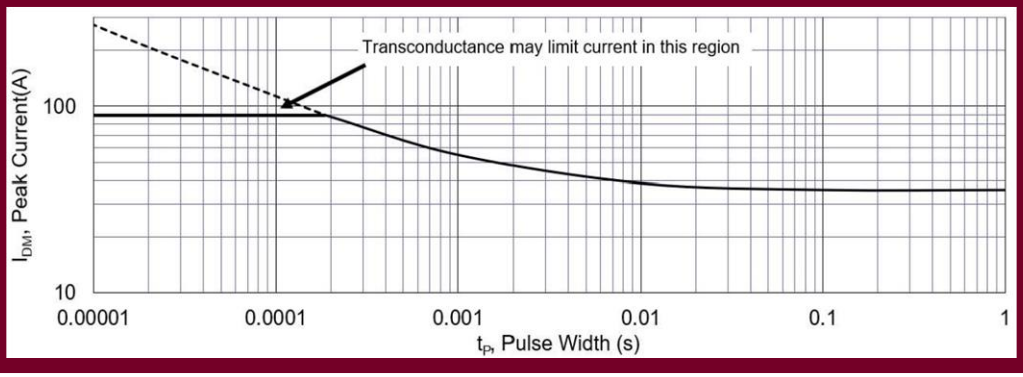


Figure 7: Typical Transfer Characteristics

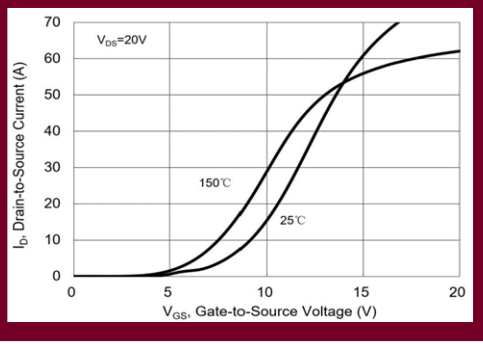


Figure 8: Typical Drain to Source ON Resistance

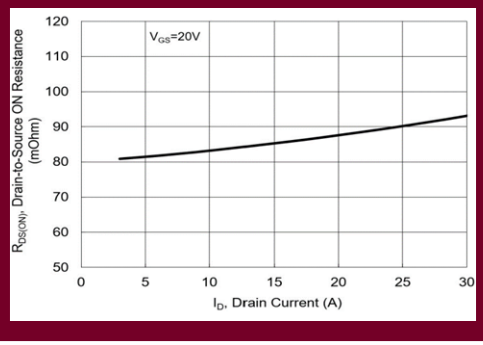


Figure 9: Typical Drain to Source ON Resistance vs Junction Temperature

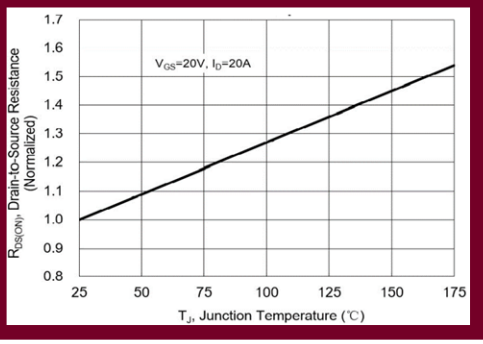
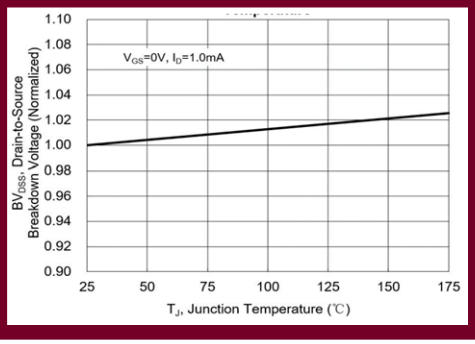


Figure 10: Typical Breakdown Voltage vs. Junction Temperature



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Figure 11: Typical Threshold Voltage vs. Junction Temperature

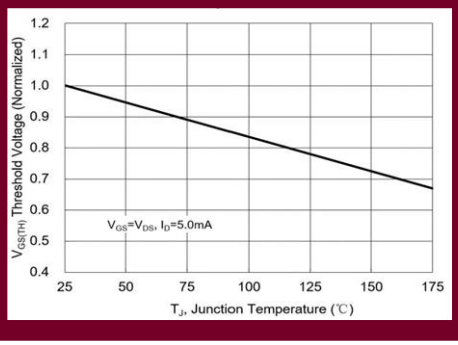


Figure 12: Typical Capacitance vs. Drain-to-Source Voltage

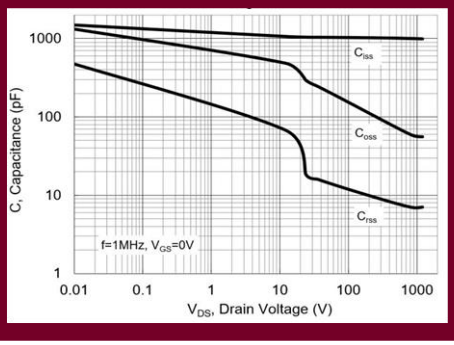


Figure 13: Maximum Forward Safe Operating Area

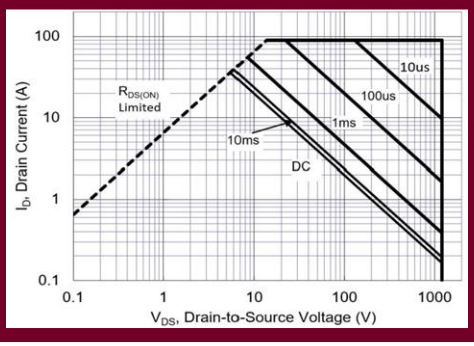
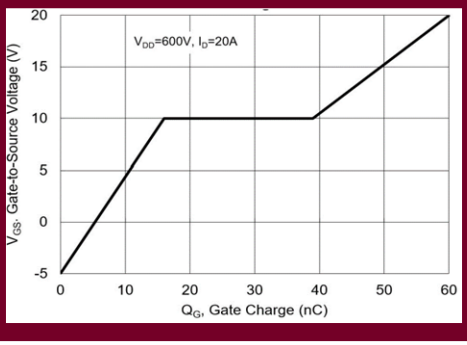


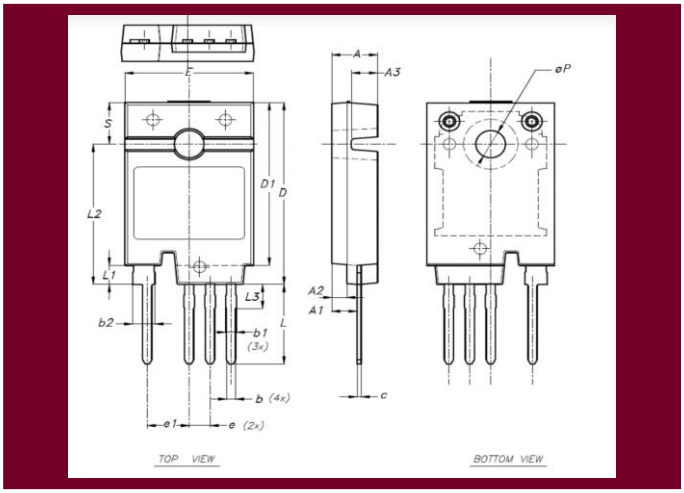
Figure 14: Typical Gate Charge vs. Gate to Source Voltage



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DIM	MIN(mm)	MAX(mm)	NOM(mm)
A	5.50	5.80	5.65
A1	2.85	3.25	3.15
A2			1.92
A3			3.18
B	0.95	1.30	1.10
B1	1.10	1.50	
B2	2.50	2.90	
C	0.40	0.80	
D	23.85	24.15	24
D1			21.50
E	15.45	15.75	15.60
E1			2.54
L			5.08
L1	10.20	10.80	
L2	2.20	2.80	2.50
L3			18.50
oP			3
S	3.55	3.65	
			5.50

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